

## CURRENT MODE PWM CONTROLLER

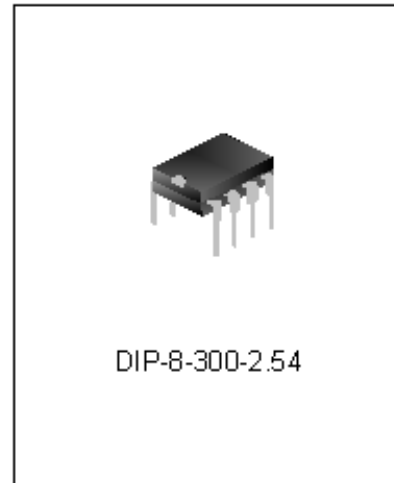
### DESCRIPTION

GGDH6802 is current mode PWM controller with built-in high-voltage MOSFET used for SMPS.

GGDH6802 has a built-in high-voltage start-up constant current source and the charge current is large.

GGDH6802 enters burst mode to reduce the standby power dissipation in light load. The switch frequency is 60KHz with jitter frequency for low EMI.

GGDH6802 integrates various protections such as under voltage lockout, lead edge blanking, over voltage protection, over current protection and over temperature protection. The circuit will restart until normal if protection occurs.



### FEATURES

- \* Built-in high voltage start-up constant current source
- \* Frequency jitter for low EMI
- \* Wide supply voltage range: 9V ~ 38V
- \* Burst mode with light load
- \* Current control mode
- \* Over voltage protection and under voltage lockout
- \* Over current protection
- \* Over temperature protection

### APPLICATIONS

- \* Off-line SMPS
- \* Non-isolated buck-boost converter
- \* Small home appliances

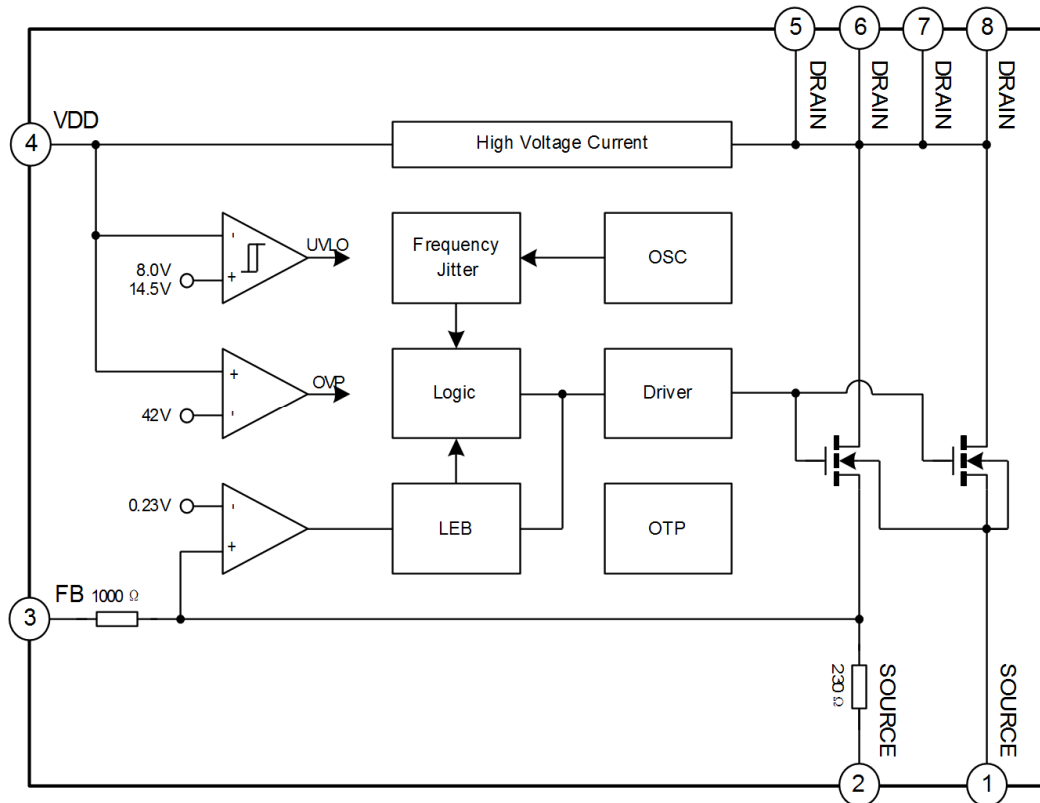
### ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
GGDH6802	DIP-8-300-2.54	GGDH6802	Pb free	Tube

### TYPICAL OUPUT POWER CAPABILITY

Part No.	195~265V		85~265V	
	Adapter	Open	Adapter	Open
GGDH6802	10W	13W	5W	8W

## BLOCK DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Characteristics	Symbol	Ratings	Unit
Drain Gate Voltage (RGS=1MΩ)	V <sub>DGR</sub>	650	V
Gate-Source (GND) Voltage	V <sub>GS</sub>	±30	V
Drain Current Pulse *	I <sub>DM</sub>	6	A
Continuous Drain Current (Tamb=25°C)	I <sub>D</sub>	1	A
Signal Pulse Avalanche Energy **	EAS	30	mJ
High Voltage Input	V <sub>HV,MAX</sub>	650	V
Power Supply Voltage	V <sub>CC,MAX</sub>	50	V
Feedback current	I <sub>FB</sub>	3	mA
Power Dissipation	P <sub>D</sub>	6.3	W
Thermal Resistance Junction-Ambient	θ <sub>ja</sub>	70	°C/W
Thermal Resistance Junction-case	θ <sub>jc</sub>	20	°C/W
Operating Junction Temperature	T <sub>J</sub>	+150	°C
Operating Temperature Range	T <sub>amb</sub>	-20~+85	°C
Storage Temperature Range	T <sub>STG</sub>	-55~+150	°C

**Note:** 1. Pulse width is limited by maximum junction temperature;

2.  $L=51\text{mH}$ ,  $T_J=25^\circ\text{C}(\text{start})$ .

**ELECTRICAL CHARACTERISTICS** (For MOSFET, unless otherwise specified,  $T_{amb} = 25^{\circ}\text{C}$ )

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=50\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V$	--	--	50	$\mu A$
		$V_{DS}=480V, V_{GS}=0V, T_{amb}=125^{\circ}\text{C}$	--	--	200	$\mu A$
Static Drain-Source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.5A$	--	8.4	--	$\Omega$
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$	--	155	--	pF
Output Capacitance	$C_{OSS}$	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$	--	23	--	pF
Reverse Transfer Capacitance	$C_{RSS}$	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$	--	0.6	--	pF
Turn On Delay Time	$T_{D(ON)}$	$V_{DD}=0.5BV_{DSS}, I_D=25\text{mA}$	--	6	--	ns
Rise Time	$T_R$	$V_{DD}=0.5BV_{DSS}, I_D=25\text{mA}$	--	13	--	ns
Turn Off Delay Time	$T_{D(OFF)}$	$V_{DD}=0.5BV_{DSS}, I_D=25\text{mA}$	--	9	--	ns
Fall Time	$T_F$	$V_{DD}=0.5BV_{DSS}, I_D=25\text{mA}$	--	17	--	ns

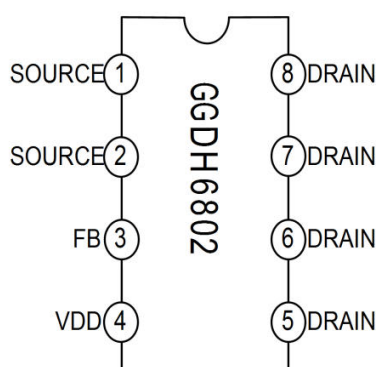
**ote:** The OL debounce Time and Soft start time is proportional to the period of switching cycle. So that, the lower RT value will bring the higher switching frequency, shorter the OL debounce Time and shorter Soft start

**ELECTRICAL CHARACTERISTICS**(Unless otherwise stated,  $V_{CC}=18V$ ;  $T_{amb}=25^{\circ}\text{C}$ )

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>High voltage start-up section</b>						
Charge current	$I_{HVC}$	$V_{CC}=0V, V_{HV}=100V$	0.5	1.0	1.2	mA
Shutdown leakage current	$I_{HVS}$	$V_{CC}=18V$	--	3	20	$\mu A$
<b>Supply section</b>						
Operating voltage range	$V_{DD}$	After start-up	9V	--	38V	V
Operating current 0	$I_{DD0}$	$I_{FB} = 2\text{mA}$ ; not switching	--	0.55	--	mA
Operating current 1	$I_{DD1}$	$I_{FB} = 0.5\text{mA}$ ; $I_D = 50\text{mA}$	--	1.00	--	mA
Shutdown threshold	$V_{DDOFF}$		7	8	9	V
Start-up threshold	$V_{DDON}$		13	14.5	16	V
Threshold hysteresis	$V_{DDHYS}$		5.8	6.5	7.2	V
Over voltage threshold	$V_{DDOVP}$		38	42	46	V
<b>PWM comparator section</b>						
$I_{FB}$ to $I_D$ current gain	$G_{ID}$		--	320	--	
Peak current limitation	$I_{DLIM}$	$V_{FB} = 0V$	0.32	0.4	0.48	A
$I_{FB}$ shutdown current	$I_{FBS}$		--	0.9	--	mA
FB Pin input impedance	$R_{FB}$	$I_D = 0\text{mA}$	--	1.2	--	k $\Omega$
Current sense delay to turn-off	$t_d$	$I_D = 0.2A$	--	200	--	ns
lead edge blanking,	$t_{LEB}$		--	500	--	ns
Minimum turn-on time	$T_{ONMIN}$		--	700	--	ns

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>Over temperature protection section</b>						
Thermal shutdown temperature	$T_{SD}$		--	155	--	°C
Thermal shutdown hysteresis	$T_{HYS}$		--	40	--	°C

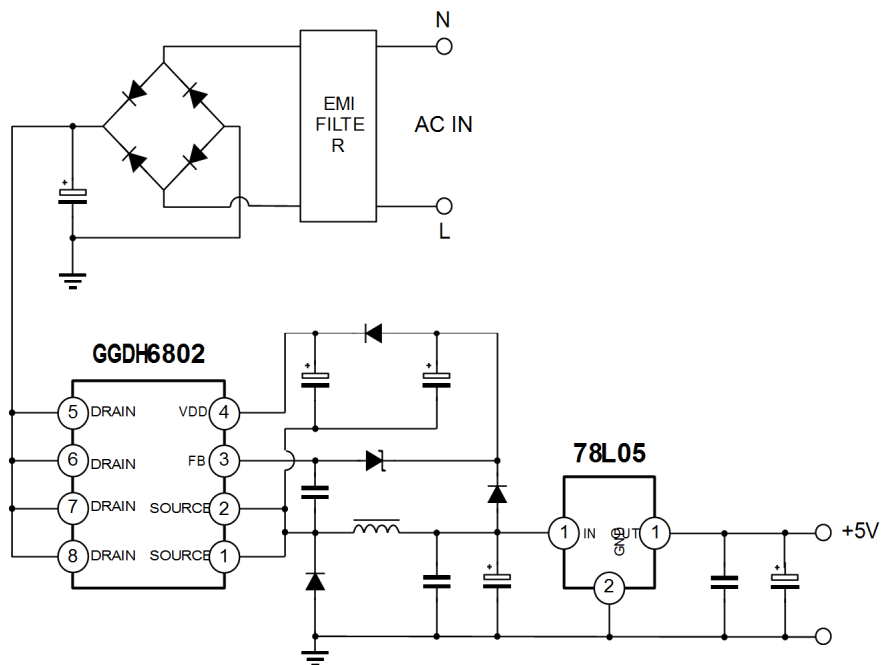
## PIN CONFIGURATION



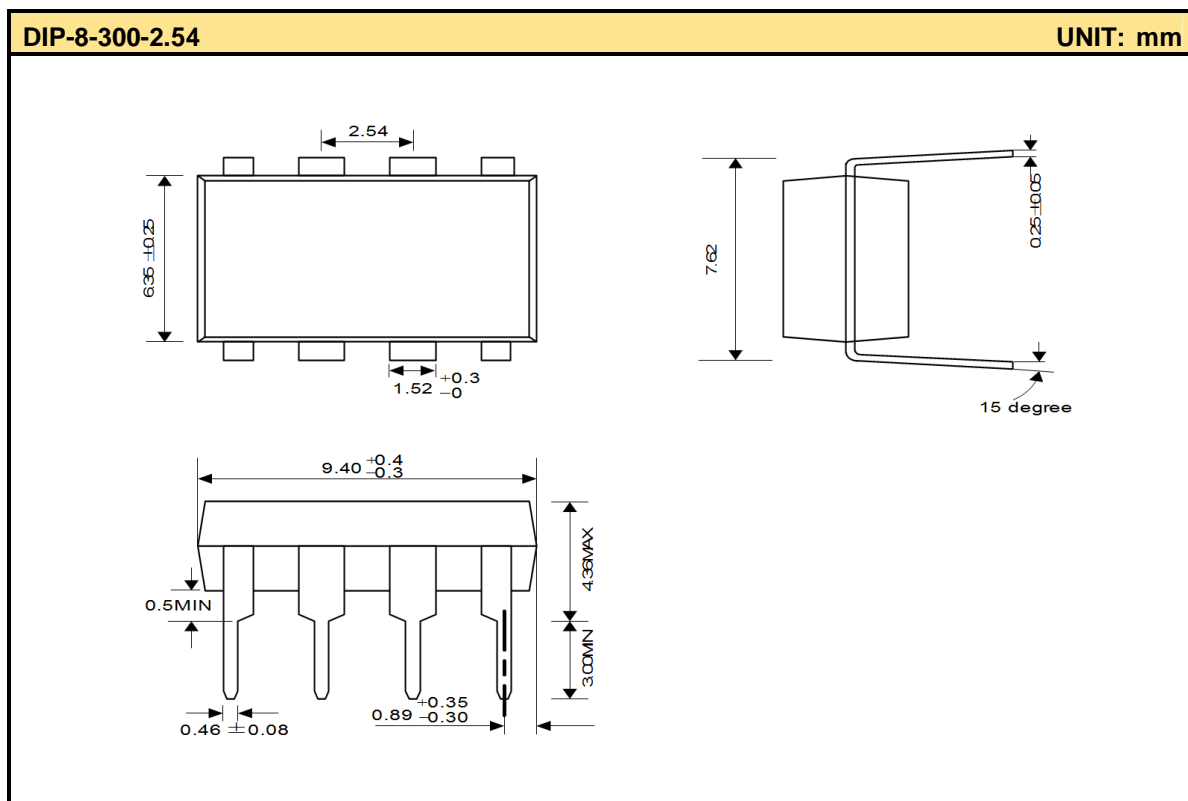
## PIN DESCRIPTION

Pin No.	Pin Name	I/O	Description
1, 2	SOURCE	I/O	Power MOSFET source and circuit ground reference.
3	FB	I	Feedback input. The useful voltage range extends from 0V to 1V, and defines the peak drain MOSFET current. The current limitation, which corresponds to the maximum drain current, is obtained for a FB pin shorted to the SOURCE pin.
4	VDD	I/O	Power supply of the control circuits.
5, 6, 7, 8	DRAIN	I/O	Power MOSFET drain. Also used by the internal high voltage current source during start up phase for charging the external VDD capacitor

## TYPICAL APPLICATION CIRCUIT



## PACKAGE OUTLINE



**MOS DEVICES OPERATING NOTES:**

Electrostatic charges may exist in many things. Please take the following preventive measures to prevent damage to the MOS electric circuit caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic discharge.
- Equipment cases should be earthed. •
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.

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